TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

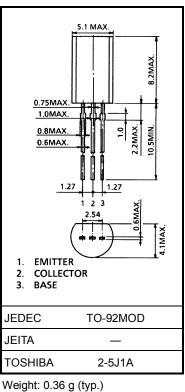
# 2SC2500

Strobe Flash Applications Medium-Power Amplifier Applications

- High DC current gain and excellent hFE linearity
   hFE (1) = 140 to 600 (VCE = 1 V, IC = 0.5 A)
   H FE (2) = 70 (...) 200 (...) (VFE = 1 V, IC = 0.5 A)
- : hFE (2) = 70 (min), 200 (typ.), (VCE = 1 V, IC = 2 A)
  Low saturation voltage: VCE (sat) = 0.5 V (max) (IC = 2 A, IB = 50 mA)

#### Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V <sub>CBO</sub>	30	V	
Collector-emitter voltage		V <sub>CES</sub>	30	V	
		V <sub>CEO</sub>	10		
Emitter-base voltage		V <sub>EBO</sub>	6	V	
Collector current	DC	۱ <sub>C</sub>	2		
	Pulsed (Note 1)	I <sub>CP</sub> 5		A	
Base current		Ι <sub>Β</sub>	0.5	А	
Collector power dissipation		Pc	900	mW	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	



Note 1: Pulse test: Pulse width = 10 ms (max), duty cycle = 30% (max)

### Electrical Characteristics (Ta = 25°C)

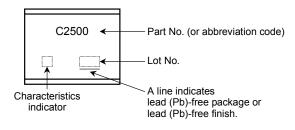
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 30 V, I <sub>E</sub> = 0	_	_	100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 6 V, I <sub>C</sub> = 0	_	-	100	nA
Collector-emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0	10	_	_	V
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>C</sub> = 1 mA, I <sub>C</sub> = 0	6	_	_	V
DC current gain	h <sub>FE (1)</sub> (Note 2)	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 0.5 A	140	_	600	
	h <sub>FE (2)</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 2 A	70	200	_	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = 2 A, I <sub>B</sub> = 50 mA	_	0.2	0.5	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 2 A	_	0.86	1.5	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 0.5 A	_	150		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz	_	27	—	pF

Note 2: hFE (1) classification A: 140 to 240, B: 200 to 330, C: 300 to 450, D: 420 to 600

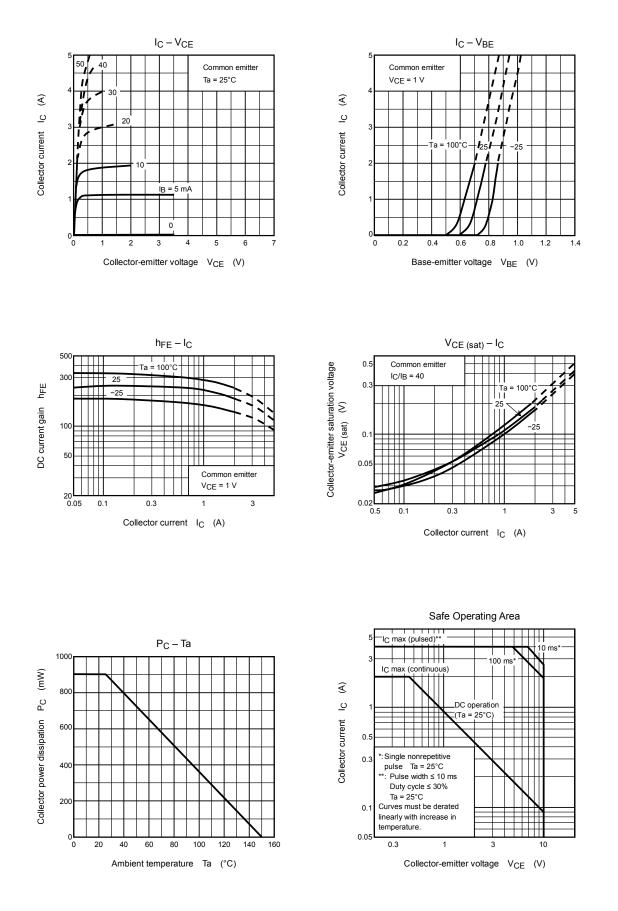
Unit: mm

## **TOSHIBA**

### Marking



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